## **Octal Bus Buffer**

The MC74VHC244 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology.

The MC74VHC244 is a noninverting 3-state buffer, and has two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $t_{PD} = 3.9 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25$ °C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.9 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V
  - Machine Model > 200 V
- Chip Complexity: 136 FETs
- Pb-Free Packages are Available\*

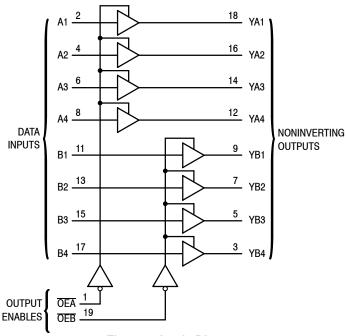


Figure 1. Logic Diagram



#### ON Semiconductor®

http://onsemi.com

#### **MARKING DIAGRAM**



SOIC-20 WB DW SUFFIX CASE 751D



TSSOP-20 DT SUFFIX CASE 948E





**CASE 967** 

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

#### **PIN ASSIGNMENT**

| 1● | 20                              | v <sub>cc</sub>                         |
|----|---------------------------------|---|
| 2  | 19                              | ) OEB                                   |
| 3  | 18                              | YA1                                     |
| 4  | 17                              | ] B4                                    |
| 5  | 16                              | YA2                                     |
| 6  | 15                              | ] B3                                    |
| 7  | 14                              | YA3                                     |
| 8  | 13                              | ] B2                                    |
| 9  | 12                              | YA4                                     |
| 10 | 11                              | ] B1                                    |
|    | 2<br>3<br>4<br>5<br>6<br>7<br>8 | 2 19 3 18 4 17 5 16 6 15 7 14 8 13 9 12 |

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the Ordering Information Table on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **FUNCTION TABLE**

| INP      | OUTPUTS |        |
|----------|---------|--------|
| OEA, OEB | A, B    | YA, YB |
| L        | L       | L      |
| L        | Н       | Н      |
| н        | X       | Z      |

#### **ORDERING INFORMATION**

| Device                   | Package                               | Shipping <sup>†</sup> |
|--------------------------|---------------------------------------|-----------------------|
| MC74VHC244DW - OBSOLETE* | SOIC-20 WB                            | 38 Units/Rail         |
| MC74VHC244DWR2           | SOIC-20 WB                            | 1000/Tape & Reel      |
| MC74VHC244DT             | TSSOP-20<br>(Pb-Free)                 | 75 Units/Rail         |
| MC74VHC244DTR2           | TSSOP-20<br>(Pb-Free)                 | 2500/Tape & Reel      |
| MC74VHC244M - OBSOLETE*  | SOIC EIAJ-20 1600 Units/Box (Pb-Free) |                       |
| MC74VHC244MEL            | SOIC EIAJ-20<br>(Pb-Free)             | 2000/Tape & Reel      |

<sup>\*</sup>This device is obsolete, information available for reference.

#### MAXIMUM RATINGS (Note 1)

| Symbol               |  | Parameter  | Value                        | Unit |
|----------------------|--|--|------------------------------|------|
| V <sub>CC</sub>      | Positive DC Supply Voltage                 |  | -0.5 to +7.0                 | V    |
| V <sub>IN</sub>      | Digital Input Voltage                      |  | -0.5 to +7.0                 | V    |
| V <sub>OUT</sub>     | DC Output Voltage                          |  | -0.5 to V <sub>CC</sub> +0.5 | V    |
| I <sub>IK</sub>      | Input Diode Current                        |  | -20                          | mA   |
| lok                  | Output Diode Current                       |  | ± 20                         | mA   |
| I <sub>OUT</sub>     | DC Output Current, per Pin                 |  | ± 25                         | mA   |
| I <sub>CC</sub>      | DC Supply Current, V <sub>CC</sub> and GND | ) Pins   | ± 75                         | mA   |
| P <sub>D</sub>       | Power Dissipation in Still Air             | SOIC<br>TSSOP  | 500<br>450                   | mW   |
| T <sub>STG</sub>     | Storage Temperature Range                  |  | -65 to +150                  | °C   |
| V <sub>ESD</sub>     | ESD Withstand Voltage                      | Human Body Model (Note 2)<br>Machine Model (Note 3)<br>Charged Device Model (Note 4) | >2000<br>>200<br>>200        | V    |
| I <sub>LATCHUP</sub> | Latchup Performance                        | Above V <sub>CC</sub> and Below GND at 125°C (Note 5)                                | ±300                         | mA   |
| $\theta_{JA}$        | Thermal Resistance, Junction-to-           | Ambient SOIC TSSOP   | 96<br>128                    | °C/W |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 3. Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.
 Tested to EIA/JESD22-A114-A

#### RECOMMENDED OPERATING CONDITIONS

| Symbol                          | Characteristics                                |  | Min | Max             | Unit |
|---------------------------------|--|--|-----|-----------------|------|
| V <sub>CC</sub>                 | DC Supply Voltage                              |  | 2.0 | 5.5             | V    |
| V <sub>IN</sub>                 | DC Input Voltage                               |  | 0   | 5.5             | V    |
| V <sub>OUT</sub>                | DC Output Voltage                              |  | 0   | V <sub>CC</sub> | V    |
| T <sub>A</sub>                  | Operating Temperature Range, all Package Types |  | -55 | 125             | °C   |
| t <sub>r</sub> , t <sub>f</sub> | Input Rise or Fall Time                        | $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$<br>$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$ | 0   | 100<br>20       | ns/V |

# DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

| Junction<br>Temperature °C | Time, Hours | Time, Years |
|----------------------------|-------------|-------------|
| 80                         | 1,032,200   | 117.8       |
| 90                         | 419,300     | 47.9        |
| 100                        | 178,700     | 20.4        |
| 110                        | 79,600      | 9.4         |
| 120                        | 37,000      | 4.2         |
| 130                        | 17,800      | 2.0         |
| 140                        | 8,900       | 1.0         |

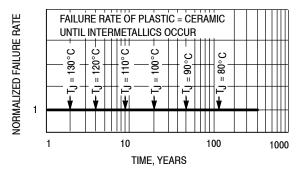


Figure 2. Failure Rate vs. Time Junction Temperature

### DC CHARACTERISTICS (Voltages Referenced to GND)

|                 |  |  | V <sub>CC</sub>   | 7                       | Γ <sub>A</sub> = 25°0 |                         | T <sub>A</sub> ≤        | 85°C                    | -55°C ≤ T               | <sub>A</sub> ≤ 125°C    |      |
|-----------------|--|--|-------------------|-------------------------|-----------------------|-------------------------|-------------------------|-------------------------|-------------------------|-------------------------|------|
| Symbol          | Parameter  | Condition  | (V)               | Min                     | Тур                   | Max                     | Min                     | Max                     | Min                     | Max                     | Unit |
| V <sub>IH</sub> | Minimum High-Level                                   |  | 2.0               | 1.5                     |                       |                         | 1.5                     | 1.5                     | 1.5                     |                         | ٧    |
|                 | Input Voltage  |  | 3.0 to<br>5.5     | V <sub>CCX</sub><br>0.7 |                       |                         | V <sub>CCX</sub><br>0.7 | V <sub>CCX</sub><br>0.7 | V <sub>CCX</sub><br>0.7 |                         |      |
| $V_{IL}$        | Maximum Low-Level                                    |  | 2.0               |                         |                       | 0.5                     |                         | 0.5                     |                         | 0.5                     | V    |
|                 | Input Voltage  |  | 3.0 to<br>5.5     |                         |                       | V <sub>CCX</sub><br>0.3 |                         | V <sub>CCX</sub><br>0.3 |                         | V <sub>CCX</sub><br>0.3 |      |
| V <sub>OH</sub> | Maximum High-Level<br>Output Voltage                 | $V_{IN} = V_{IH}$ or $V_{IL}$<br>$I_{OH} = -50 \mu A$            | 2.0<br>3.0        | 1.9<br>2.9              | 2.0<br>3.0            |                         | 1.9<br>2.9              |                         | 1.9<br>2.9              |                         | ٧    |
|                 | Culput Voltage                                       | 10H = 00 μ/ (  | 4.5               | 4.4                     | 4.5                   |                         | 4.4                     |                         | 4.4                     |                         |      |
|                 |  | $V_{IN} = V_{IH} \text{ or } V_{IL}$<br>$I_{OH} = -4 \text{ mA}$ | 3.0               | 2.58                    |                       |                         | 2.48                    |                         | 2.34                    |                         |      |
|                 |  | I <sub>OH</sub> = -8 mA  | 4.5               | 3.94                    |                       |                         | 3.8                     |                         | 3.66                    |                         |      |
| V <sub>OL</sub> | Maximum Low-Level<br>Output Voltage                  | $V_{IN} = V_{IH} \text{ or } V_{IL}$<br>$I_{OL} = 50 \mu A$      | 2.0<br>3.0<br>4.5 |                         | 0.0<br>0.0<br>0.0     | 0.1<br>0.1<br>0.1       |                         | 0.1<br>0.1<br>0.1       |                         | 0.1<br>0.1<br>0.1       | V    |
|                 |  | V <sub>IN</sub> = V <sub>IH</sub> or V <sub>II</sub>             | 4.5               |                         | 0.0                   | 0.1                     |                         | 0.1                     |                         | 0.1                     |      |
|                 |  | I <sub>OH</sub> = 4 mA<br>I <sub>OH</sub> = 8 mA                 | 3.0<br>4.5        |                         |                       | 0.36<br>0.36            |                         | 0.44<br>0.44            |                         | 0.52<br>0.52            |      |
| I <sub>IN</sub> | Input Leakage Current                                | V <sub>IN</sub> = 5.5 V or GND                                   | 0 to<br>5.5       |                         |                       | ±0.1                    |                         | ±1.0                    |                         | ±1.0                    | μΑ   |
| I <sub>OZ</sub> | Maximum 3-State<br>Leakage Current                   | $V_{IN} = V_{IH}$ or $V_{IL}$                                    | 5.5               |                         |                       | ±0.25                   |                         | ±2.5                    |                         | ±2.5                    | μΑ   |
|                 |  | $V_{OUT} = V_{CC}$ or GND  |                   |                         |                       |                         |                         |                         |                         |                         |      |
| I <sub>CC</sub> | Maximum Quiescent<br>Supply Current<br>(per package) | $V_{IN} = V_{CC}$ or GND   | 5.5               |                         |                       | 4.0                     |                         | 40.0                    |                         | 40.0                    | μΑ   |

#### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

|  |   |   |                    |     | T <sub>A</sub> = 25° | С            | T <sub>A</sub> ≤ | 85°C         |            | C ≤ T <sub>A</sub><br>25°C |      |
|--|---|---|--------------------|-----|----------------------|--------------|------------------|--------------|------------|----------------------------|------|
| Symbol                                   | Parameter   | Test Conditions   | s                  | Min | Тур                  | Max          | Min              | Max          | Min        | Max                        | Unit |
| t <sub>PLH</sub> ,<br>t <sub>PHL</sub>   | Maximum Propagation<br>Delay, A to YA or                                | $V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L$ $C_L$  | = 15 pF<br>= 50 pF |     | 5.8<br>8.3           | 8.4<br>11.9  | 1.0<br>1.0       | 10.0<br>13.5 | 1.0<br>1.0 | 11.0<br>14.5               | ns   |
|  | B to YB   | V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> C <sub>L</sub>   | = 15 pF<br>= 50 pF |     | 3.9<br>5.4           | 5.5<br>7.5   | 1.0<br>1.0       | 6.5<br>8.5   | 1.0<br>1.0 | 7.5<br>9.5                 | -    |
| t <sub>PZL</sub> ,<br>t <sub>PZH</sub>   | Output Enable Time OEA to YA or   | $\begin{aligned} &V_{CC} = 3.3 \pm 0.3 \ V & C_L \\ &R_L = 1 \ k\Omega & C_L \end{aligned}$             |                    |     | 6.6<br>9.1           | 10.6<br>14.1 | 1.0<br>1.0       | 12.5<br>16.0 | 1.0<br>1.0 | 13.5<br>17.0               | ns   |
|  | OEB to YB   | $\begin{aligned} V_{CC} &= 5.0 \pm 0.5 \text{ V} & C_L \\ R_L &= 1 \text{ k}\Omega & C_L \end{aligned}$ |                    |     | 4.7<br>6.2           | 7.3<br>9.3   | 1.0<br>1.0       | 8.5<br>10.5  | 1.0<br>1.0 | 9.5<br>11.5                | •    |
| t <sub>PLZ</sub> ,<br>t <sub>PHZ</sub>   | Output Disable Time OEA to YA or  | $\begin{aligned} V_{CC} &= 3.3 \pm 0.3 \text{ V} & C_L \\ R_L &= 1 \text{ k}\Omega \end{aligned}$       | = 50 pF            |     | 10.3                 | 14.0         | 1.0              | 16.0         | 1.0        | 17.0                       | ns   |
|  | OEB to YB   | $V_{CC} = 5.0 \pm 0.5 \text{ V}  C_L$ $R_L = 1 \text{ k}\Omega$   | = 50 pF            |     | 6.7                  | 9.2          | 1.0              | 10.5         | 1.0        | 11.5                       |      |
| t <sub>OSLH</sub> ,<br>t <sub>OSHL</sub> | Output to Output Skew   | V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> (Note 6)   | = 50 pF            |     |                      | 1.5          |                  | 1.5          |            | 1.5                        | ns   |
|  |   | $V_{CC} = 5.0 \pm 0.5 \text{ V}$ C <sub>L</sub> (Note 6)  | = 50 pF            |     |                      | 1.0          |                  | 1.0          |            | 1.5                        |      |
| C <sub>in</sub>                          | Maximum Input<br>Capacitance  |   |                    |     | 4                    | 10           |                  | 10           |            | 10                         | pF   |
| C <sub>out</sub>                         | Maximum Three-State Output Capacitance (Output in High-Impedance State) |   |                    |     | 6                    |              |                  |              |            |                            | pF   |

|          |  | Typical @ 25°C, V <sub>CC</sub> = 5.0V |    |  |
|----------|--|--|----|--|
| $C_{PD}$ | Power Dissipation Capacitance (Note 7) | 19                                     | pF |  |

<sup>6.</sup> Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.

### NOISE CHARACTERISTICS (Input $t_f$ = $t_f$ = 3.0 ns, $C_L$ = 50 pF, $V_{CC}$ = 5.0 V)

|                  |  | T <sub>A</sub> = 25°C |      |      |
|------------------|--|-----------------------|------|------|
| Symbol           | Parameter                                    | Тур                   | Max  | Unit |
| V <sub>OLP</sub> | Quiet Output Maximum Dynamic V <sub>OL</sub> | 0.6                   | 0.9  | V    |
| V <sub>OLV</sub> | Quiet Output Minimum Dynamic V <sub>OL</sub> | -0.6                  | -0.9 | V    |
| V <sub>IHD</sub> | Minimum High Level Dynamic Input Voltage     |                       | 3.5  | V    |
| V <sub>ILD</sub> | Maximum Low Level Dynamic Input Voltage      |                       | 1.5  | V    |

<sup>7.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per bit). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

### **SWITCHING WAVEFORMS**

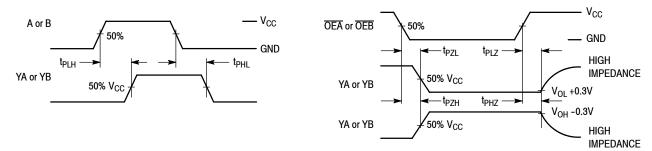
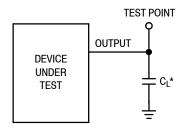


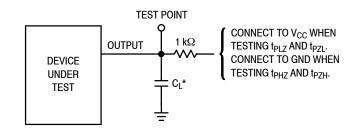
Figure 3. Switching Waveform

Figure 4. Switching Waveform

#### **TEST CIRCUITS**



\*Includes all probe and jig capacitance



\*Includes all probe and jig capacitance

Figure 5. Test Circuit

Figure 6. Test Circuit

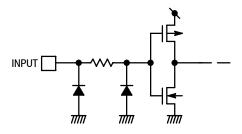
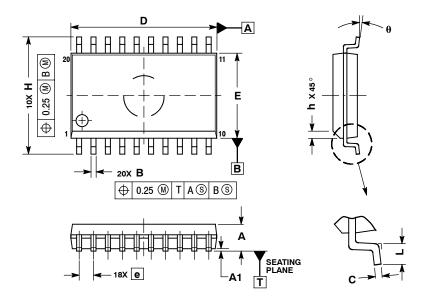


Figure 7. Input Equivalent Circuit

#### **OUTLINE DIMENSIONS**

#### SOIC-20 WB **DW SUFFIX** CASE 751D-05 ISSUE G



- NOTES:
  1. DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- PHO I HUSION.

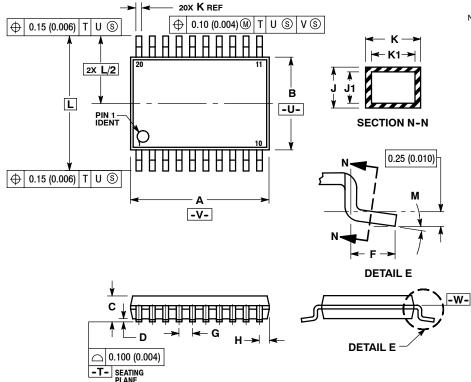
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

  DIMENSION B DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE PROTRUSION
  SHALL BE 0.13 TOTAL IN EXCESS OF B

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

|     | MILLIMETERS |       |  |  |  |
|-----|-------------|-------|--|--|--|
| DIM | MIN         | MAX   |  |  |  |
| Α   | 2.35        | 2.65  |  |  |  |
| A1  | 0.10        | 0.25  |  |  |  |
| В   | 0.35        | 0.49  |  |  |  |
| C   | 0.23        | 0.32  |  |  |  |
| D   | 12.65       | 12.95 |  |  |  |
| E   | 7.40        | 7.60  |  |  |  |
| е   | 1.27        | BSC   |  |  |  |
| Н   | 10.05       | 10.55 |  |  |  |
| h   | 0.25        | 0.75  |  |  |  |
| L   | 0.50        | 0.90  |  |  |  |
| θ   | 0°          | 7 °   |  |  |  |

#### TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE B**



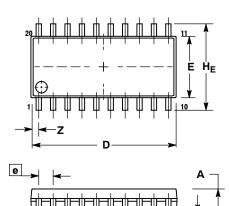
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION:
- MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION
  SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

|     | MILLIN | IETERS | INCHES    |       |  |
|-----|--------|--------|-----------|-------|--|
| DIM | MIN    | MAX    | MIN       | MAX   |  |
| Α   | 6.40   | 6.60   | 0.252     | 0.260 |  |
| В   | 4.30   | 4.50   | 0.169     | 0.177 |  |
| С   |        | 1.20   |           | 0.047 |  |
| D   | 0.05   | 0.15   | 0.002     | 0.006 |  |
| F   | 0.50   | 0.75   | 0.020     | 0.030 |  |
| G   | 0.65   | BSC    | 0.026     | BSC   |  |
| Н   | 0.27   | 0.37   | 0.011     | 0.015 |  |
| J   | 0.09   | 0.20   | 0.004     | 0.008 |  |
| J1  | 0.09   | 0.16   | 0.004     | 0.006 |  |
| K   | 0.19   | 0.30   | 0.007     | 0.012 |  |
| K1  | 0.19   | 0.25   | 0.007     | 0.010 |  |
| L   | 6.40   | BSC    | 0.252 BSC |       |  |
| M   | 0°     | 8°     | 0°        | 8°    |  |

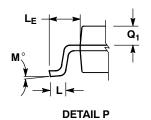
#### **OUTLINE DIMENSIONS**

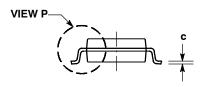
**SOIC EIAJ-20 M SUFFIX** CASE 967-01 ISSUE O



0.10 (0.004)

0.13 (0.005) M





#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) DED RISE.
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
  PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018).

|                | MILLIMETERS |       | INCHES    |       |
|----------------|-------------|-------|-----------|-------|
| DIM            | MIN         | MAX   | MIN       | MAX   |
| Α              |             | 2.05  |           | 0.081 |
| A <sub>1</sub> | 0.05        | 0.20  | 0.002     | 0.008 |
| b              | 0.35        | 0.50  | 0.014     | 0.020 |
| С              | 0.18        | 0.27  | 0.007     | 0.011 |
| D              | 12.35       | 12.80 | 0.486     | 0.504 |
| Е              | 5.10        | 5.45  | 0.201     | 0.215 |
| е              | 1.27 BSC    |       | 0.050 BSC |       |
| HE             | 7.40        | 8.20  | 0.291     | 0.323 |
| L              | 0.50        | 0.85  | 0.020     | 0.033 |
| LE             | 1.10        | 1.50  | 0.043     | 0.059 |
| M              | 0 °         | 10°   | 0 °       | 10°   |
| $Q_1$          | 0.70        | 0.90  | 0.028     | 0.035 |
| Z              |             | 0.81  |           | 0.032 |

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